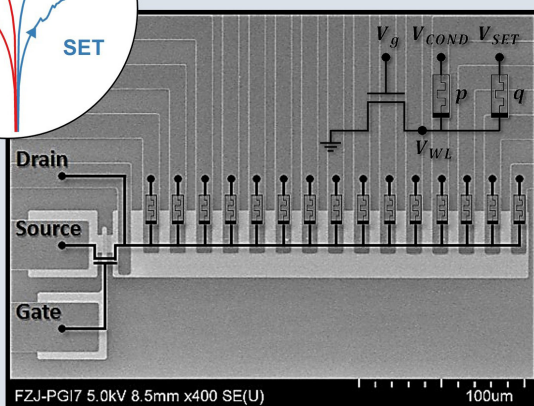
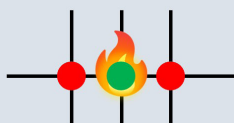
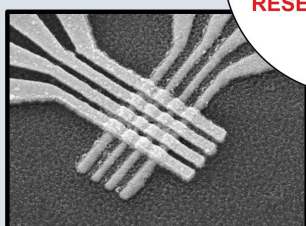
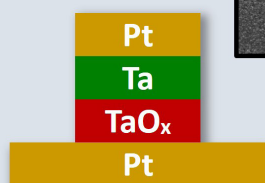
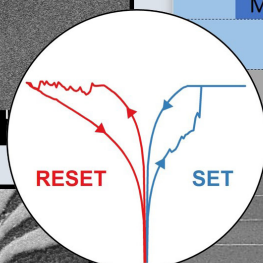
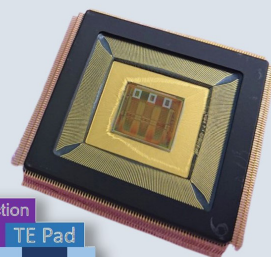
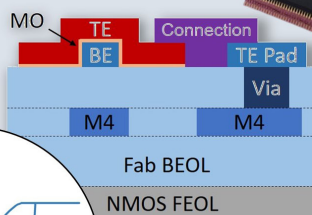
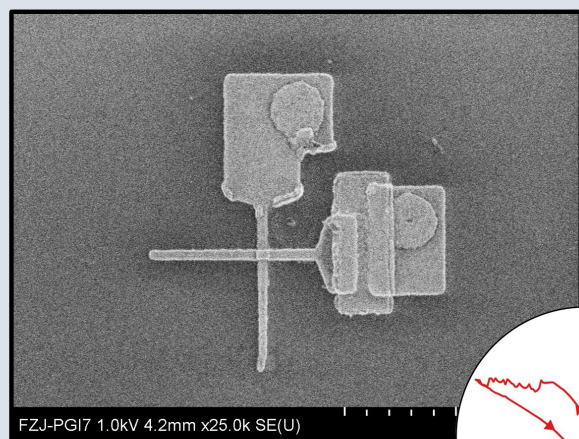




Redox-based Random Access Memory Arrays for Computing-In-Memory and Neuromorphic Computing

Hsin-Yu Chen

Information

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